

9.3 Summary

9.3.1 Summary to: 9. Optoelectronics

Optoelectronics has *two* basic branches:

1. Light in \Rightarrow electrical signal out:
 - **Optical sensors** as single elements
 - "**CCD**" chips in "megapixel" matrices.
2. Electricity in \Rightarrow light out; in two paradigmatic versions:
 - **LED's**
 - **Laser** diodes

Here we only look at the second branch.

- The semiconductors of choice are mostly the **III-V's**, usually in single-crystalline perfect thin films.
- The present day (**2008**) range of wavelength covers the **IR** to near **UV**.
- Indirect semiconductors like **GaP** can be used too, if some "tricks" are used.

The **index of refraction** $n=(\epsilon)^{1/2}$ and thus the dielectric constant ϵ become important

- Semiconductors have a relatively large index of refraction at photon energies below the bandgap of $n \approx 3 - 4$.
- Diamond has the highest n in the visible region

The **thermal conductivity** becomes important because for generating light one needs **power** (which we avoided as much as possible for signal processing with **Si**!)

- Again, diamond has the highest thermal conductivity of all known materials - **5** times better than **Cu**!

LED's come as cheap little "indicator" lights and recently also as replacement for "light bulbs".

- Intense white light from **LED's** becomes possible, Advantages: High efficiencies and long life time
- The key was the "taming" of the **GaN** material system for blue and **UV LED's**.

LED's based on organic semiconductors (**OLED**) are rapidly appearing in **OLED** based displays.

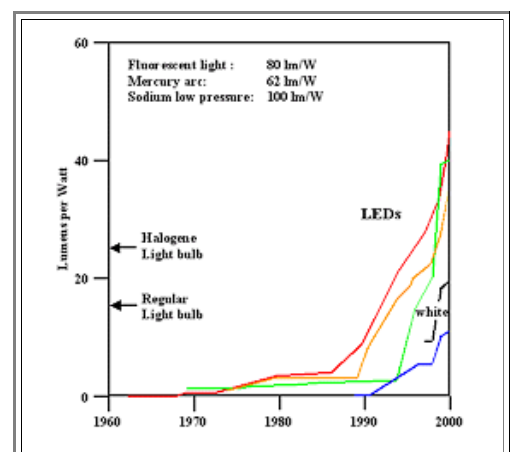
- **Advantage:** High efficiencies because of active light generation.
- **Problem:** Product life time; sensitivity to air.

Semiconductor "Diode" **Lasers** are high-power" **LED's** plus "mirrors"

- **Advantage:** Small and cheap.
- **Problems:** Low power, "Quality".

	Wavelength (nm)	Typical Semiconductor
Infrared	880	GaAlAs/GaAs
Red	660 - 633	GaAlAs/GaAs
Orange to Yellow	612 - 585	AlGaInP GaAsP/GaP GaAsP/GaP
Green	555	GaP
Blue to Ultraviolet	470 - 395	GaN/SiC GaN/SiC InGaN/SiC

Typical Semiconductor	Dielectric constant	Thermal conductivity [W/cm · K]
Si	11.9	1.5
GaAs	13.1	0,45
GaP	11.1	1.1
GaN	8.9	1.3
SiC	10	5
C (Diamond)	5.8	22

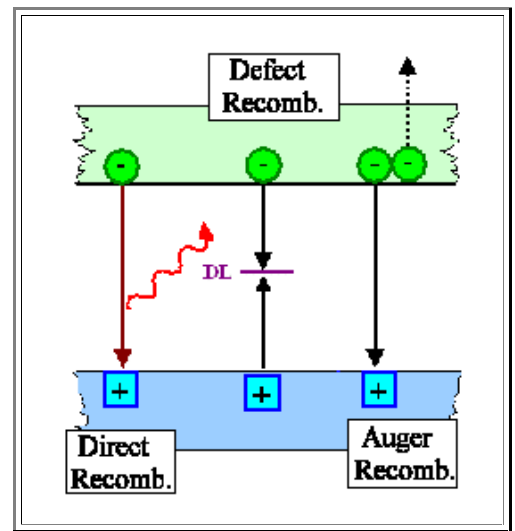


Enabling technology for
CD / DVD / Blue ray / ...
memory technologies!

There are always several recombination channels active in parallel

- Direct **band-band recombination**; *producing light*.
- **Defect recombination**; *not* producing light.
- **Auger recombination**; *not* producing light.
- "Exotic" mechanisms like **exciton recombination**; producing light in *indirect* semiconductors like GaP

High efficiency LED's need optimized recombination.

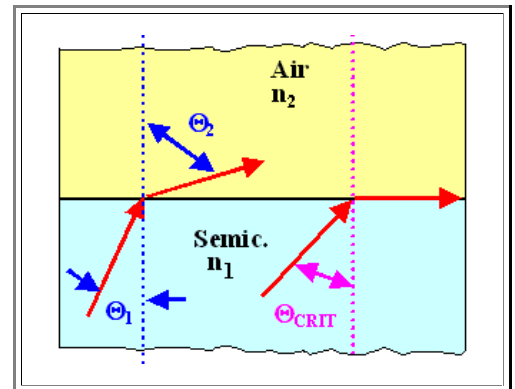


Without "tricks" only a fraction of the light produced gets out of the semiconductor

- Index grating is essential
- Avoiding re-absorption is essential
- Defined recombination volumes are important

Hetero junctions of the **NnP** or **NpP** type are the solution, but create problems of their own

- Hetero-interfaces must be defect free \Rightarrow Avoid misfit dislocations!



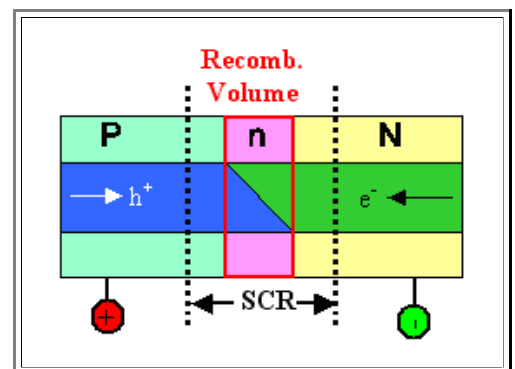
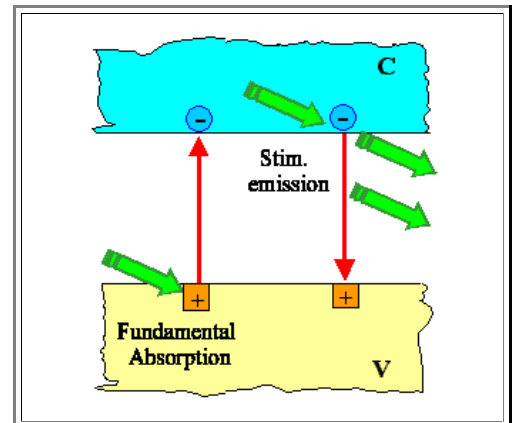
Laser diodes are similar to LED's but need to meet two additional conditions

1. The rate of **Stimulated emission**, a new process predicted by A. Einstein concerning the interaction of light and electrons in the conduction band, must be at least as large as the rate of **fundamental absorption**

- *Stimulated emission* results in *two fully coherent* photons for *one* incoming photon and thus allows optical *amplification*.
- Strong stimulated emission his requires large non-equilibrium electron concentrations in the conduction band. \Rightarrow strong "pumping" is necessary, moving electrons up to the conduction band just as fast as they disappear by recombination.
- In semiconductor junctions pumping can be "easily" achieved by very large injection currents across a forwardly biased (hetero) junction. \Rightarrow cooling problem!

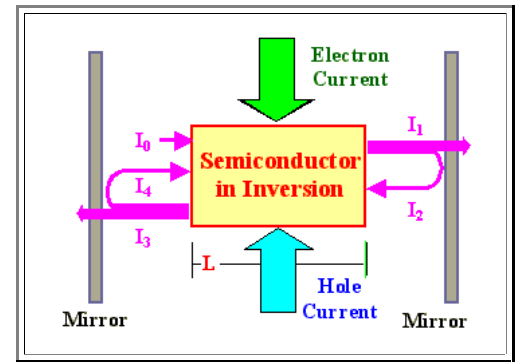
2. There must be some feed-back that turns an (optical) amplifier into an oscillator for one frequency

- *Feed-back* is achieved by partially transparent mirrors.



- Monochromatic output is achieved by the optical resonator formed by two exactly plan-parallel mirrors
- Only wavelengths $\lambda = 2L/i$ (i =integer) that "fit" into the cavity will be able to exist. Together with the condition $h\nu = hc/\lambda = E_g$ the Laser wavelength is given

➤ Semiconductor Lasers now span the range from **IR** to **UV**; essential materials are all **III-V's**, in particular the **GaN** family.



➤ **Molecular beam epitaxy** is the deposition method of choice for epitaxial multilayer structures

Exercise 9.3-1

All Quick Questions to 9.